

PATENT APPLICATION
Attorney Docket No.: 2000.008.00/US

Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT FORM PTO-1449 (Modified) <i>(USE AS MANY SHEETS AS NECESSARY)</i>				Complete If Known	
SHEET	1	OF	1	Application Number	10/620887
				Filing Date	September 25, 2003
				First Named Inventor	Kevin J. Yang
				Art Unit	2810
				Examiner Name	WOJCIĘCZOWICZ
				Attorney Docket Number	2000.008.00/US

U.S. PATENT DOCUMENTS

Examiner Initials*	Cite No.1	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number- Kind Code (If known)			
GD		US 6,462,359	10-08-02	Nemati et al.	—
		US 6,229,161	05-08-01	Nemati et al.	—
GD		US 4,323,793	04-06-82	Schutten et al.	—

OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No.1	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T2
GD		S. Lombardo et al., <i>High Temperature Annealing Effects on the Electrocal Characteristics of C Implanted Si</i> ; J. Appl. Phys. Vol. 79, No. 7, pp. 34643469, April 1, 1996.	
		Ibrahim Ban et al.; <i>Effects of Carbon Implantation on Generation Lifetime in Silicon</i> ; Appl. Phys. Lett.; Vol. 68, No. 4, pp. 499-501, Jan. 22, 1996.	
		American Microsemiconductor, <i>Tunnel Diode and Back Diode Tutorial</i> ; at www.americanmicrosemi.com/tutorials/tunneldiode.htm ; July 31, 2003.	
GD		Alan SEABAUGH; <i>Silicon-Based Tunnel Diodes and integrated Circuits</i> ; University of Notre Dame; at http://www.nd.edu/~nano/0a1003QFDpaper_v1.pdf ; July 31, 2003.	

Examiner Signature	<i>GD</i>	Date Considered	7-1-05
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